

• General Description

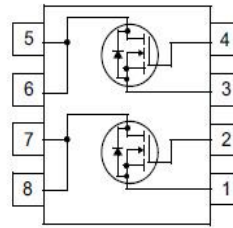
The ZMD68303S combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

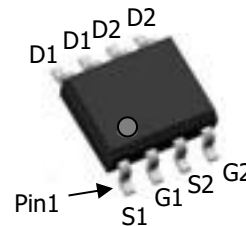
- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Dual DIE in one package

• Application

- Power Management in Notebook Computer,
- Portable Equipment and Battery Powered Systems
- Wireless Charging

• Product Summary


$V_{DS1} = 30V$
 $V_{DS2} = 30V$
 $R_{DS(ON)1} = 5m\Omega$
 $R_{DS(ON)2} = 5m\Omega$
 $I_{D1} = 18A$
 $I_{D2} = 18A$



SOP8

• Ordering Information:

Part NO.	ZMD68303S
Marking	ZMD68303
Packing Information	REEL TAPE
Basic ordering unit (pcs)	4000

• Absolute Maximum Ratings ($T_c = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	18	A
	$I_{D@TC=75^\circ C}$	14	A
	$I_{D@TC=100^\circ C}$	11.3	A
Pulsed Drain Current ^①	I_{DM}	54	A
Total Power Dissipation($TC=25^\circ C$)	$P_D@TC=25^\circ C$	3.6	W
Total Power Dissipation($TA=25^\circ C$)	$P_D@TA=25^\circ C$	0.69	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	80	mJ



Avalanche Current	I_{AS} I_{AR}	40	A
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•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2.5	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	70	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 18A$		5.0	6.5	m Ω
		$V_{GS} = 4.5V, I_D = 16A$		7.0	9.0	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 25V, I_D = 4A$		16		s
Source-drain voltage	V_{SD}	$I_S = 18A$			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	f = 1MHz	-	1500	-	pF
Output capacitance	C_{oss}		-	280	-	
Reverse transfer capacitance	C_{rss}		-	140	-	

•Gate Charge characteristics($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 25V$	-	16	-	nC
Gate - Source charge	Q_{gs}	$I_D = 8A$	-	5	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 10V$	-	8	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Fig.1 Power Dissipation

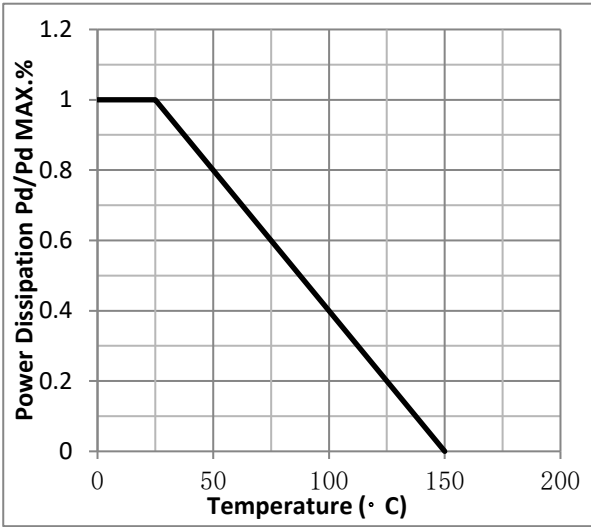


Fig.2 Typical output Characteristics

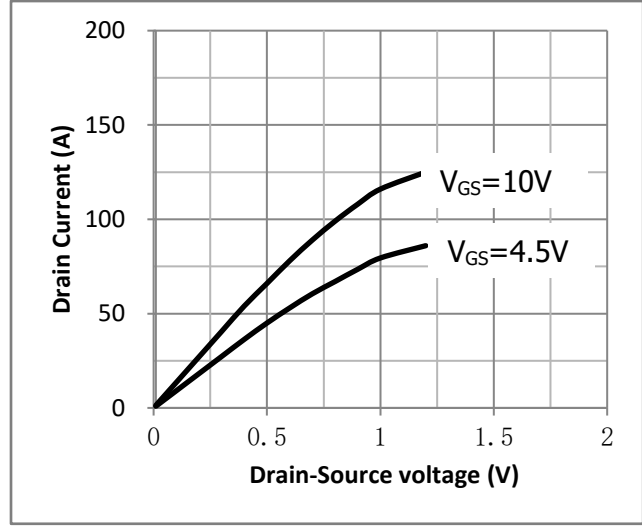


Fig.3 Threshold Voltage V.S Junction Temperature

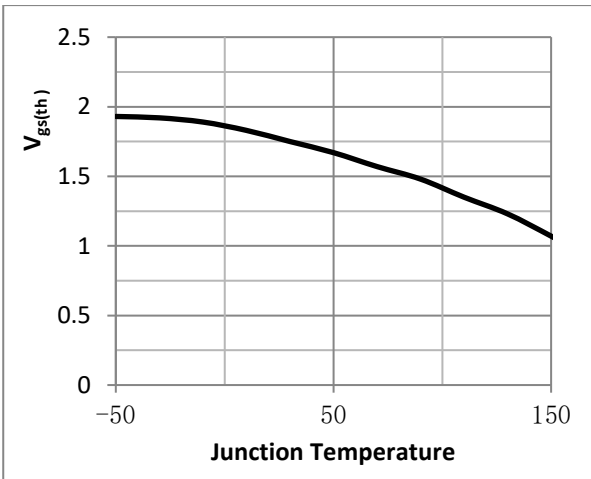


Fig.4 Resistance V.S Drain Current

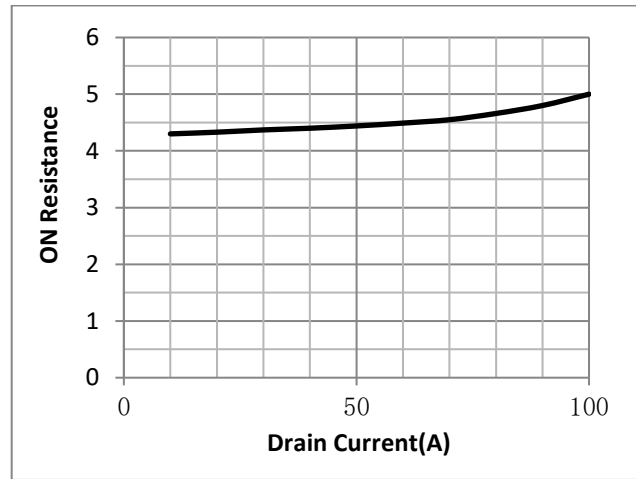


Fig.5 On-Resistance VS Gate Source Voltage

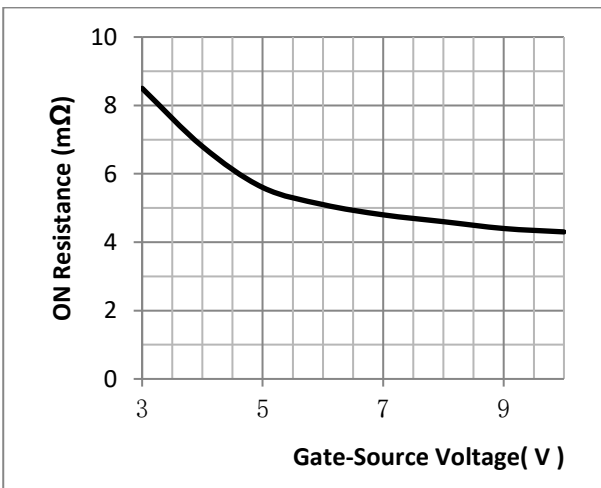


Fig.6 On-Resistance V.S Junction Temperature

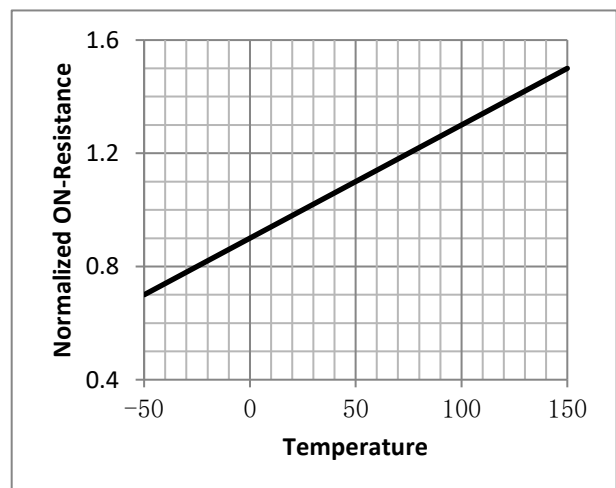


Fig.7 Switching Time Measurement Circuit

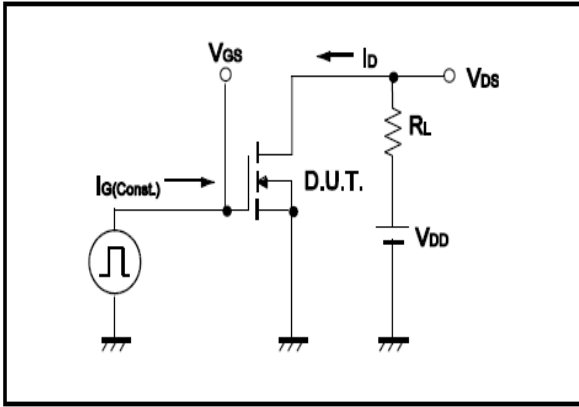


Fig.8 Gate Charge Waveform

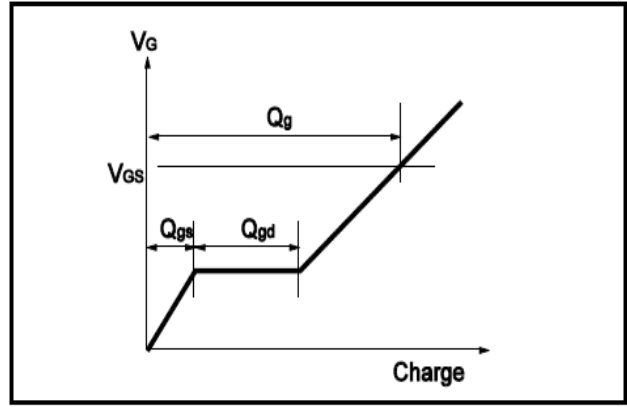


Fig.9 Switching Time Measurement Circuit

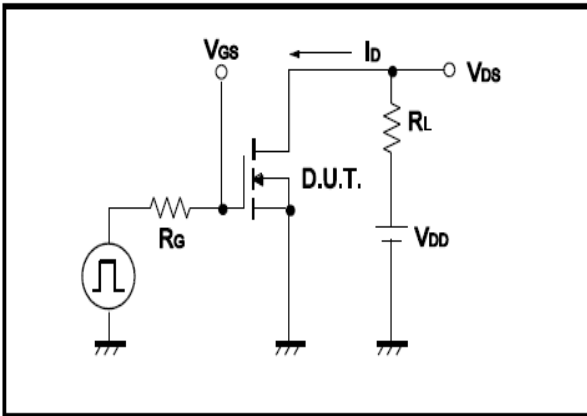


Fig.10 Gate Charge Waveform

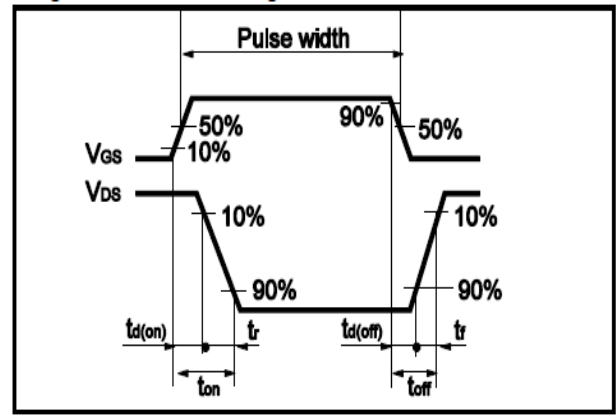


Fig.11 Avalanche Measurement Circuit

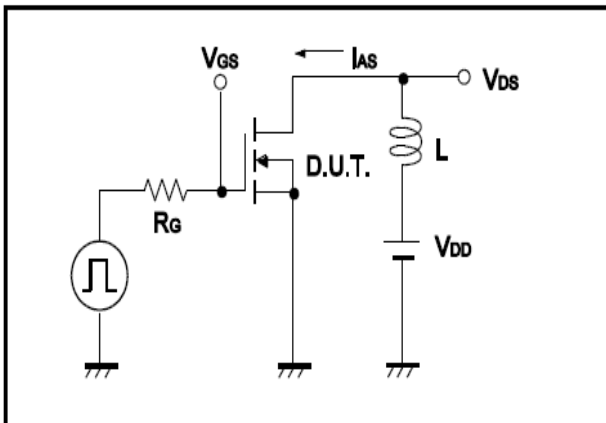
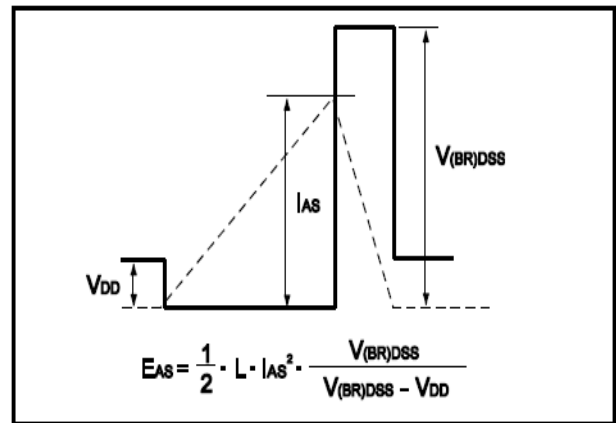


Fig.12 Avalanche Waveform



●Dimensions(SOP8)

Unit: mm

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.25	C	1.30		1.75
A1	0.37		0.49	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.10	0.20	0.23
B1	3.80		4.10	D		1.05	
B2		5.00		D1	0.40		0.62

